

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM850-251CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 92.75 V/m; Power Drift = -0.04 dB

PMF = 2.830 is applied.

E-field emissions = 205.2 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

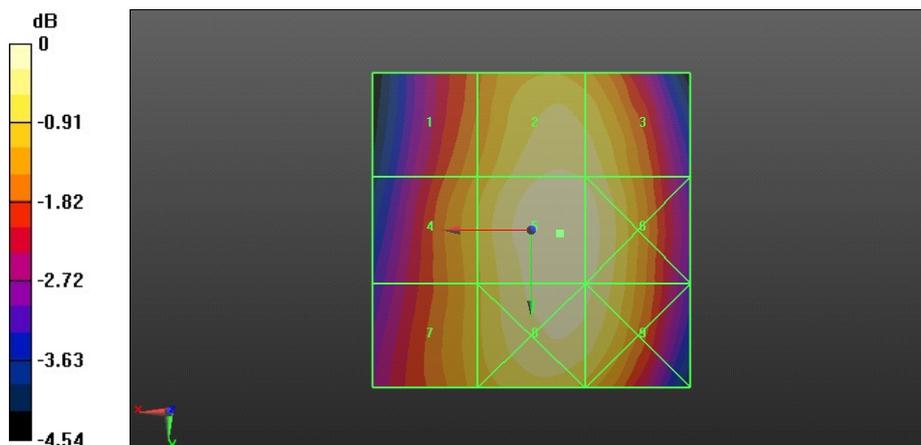
Grid 1 M3 179.8 V/m	Grid 2 M3 199.4 V/m	Grid 3 M3 197.6 V/m
Grid 4 M3 185.6 V/m	Grid 5 M3 205.2 V/m	Grid 6 M3 202.8 V/m
Grid 7 M3 183.5 V/m	Grid 8 M3 203.3 V/m	Grid 9 M3 200.3 V/m

Cursor:

Total = 205.2 V/m

E Category: M3

Location: -4.5, 0.5, 8.7 mm



0 dB = 205.2 V/m = 46.25 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM850-190CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 85.79 V/m; Power Drift = -0.07 dB

PMF = 2.830 is applied.

E-field emissions = 191.5 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

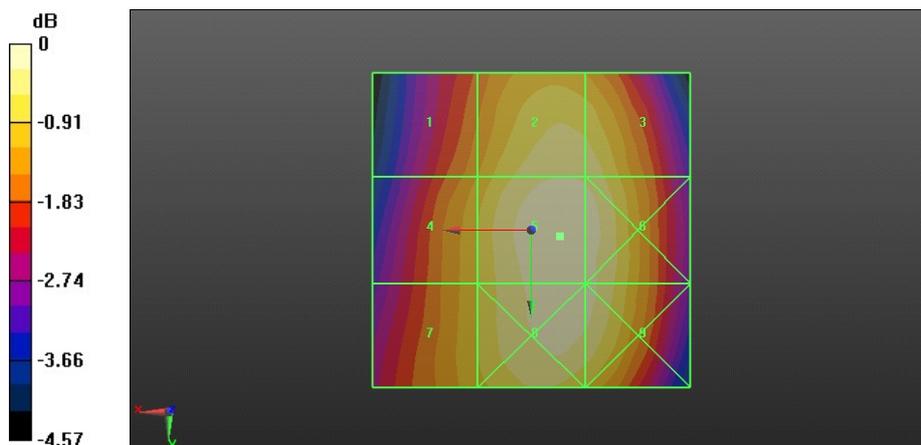
Grid 1 M3 166.4 V/m	Grid 2 M3 184.8 V/m	Grid 3 M3 183.8 V/m
Grid 4 M3 172.7 V/m	Grid 5 M3 191.5 V/m	Grid 6 M3 189.2 V/m
Grid 7 M3 172.6 V/m	Grid 8 M3 190.6 V/m	Grid 9 M3 188.0 V/m

Cursor:

Total = 191.5 V/m

E Category: M3

Location: -4.5, 1, 8.7 mm



0 dB = 191.5 V/m = 45.64 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM850-128CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 76.12 V/m; Power Drift = -0.06 dB

PMF = 2.830 is applied.

E-field emissions = 168.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

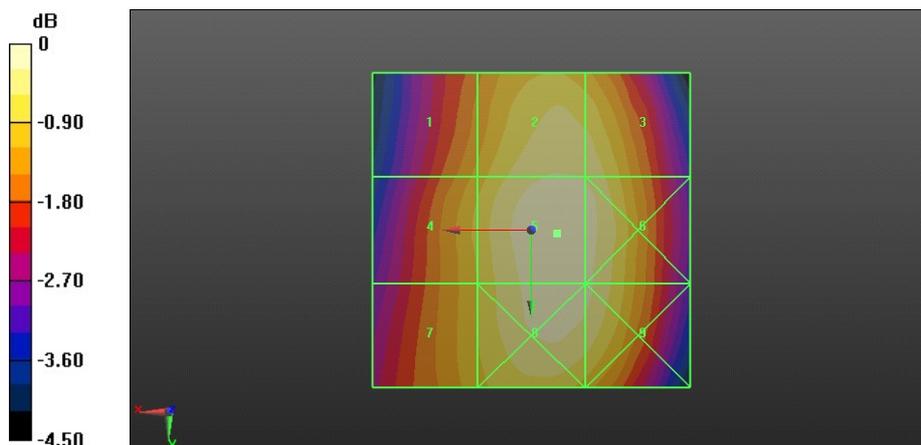
Grid 1 M4 149.2 V/m	Grid 2 M3 163.7 V/m	Grid 3 M3 162.7 V/m
Grid 4 M3 154.1 V/m	Grid 5 M3 168.9 V/m	Grid 6 M3 166.0 V/m
Grid 7 M3 152.5 V/m	Grid 8 M3 167.2 V/m	Grid 9 M3 164.9 V/m

Cursor:

Total = 168.9 V/m

E Category: M3

Location: -4, 0.5, 8.7 mm



0 dB = 168.9 V/m = 44.55 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM850-251CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 91.31 V/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

E-field emissions = 204.4 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

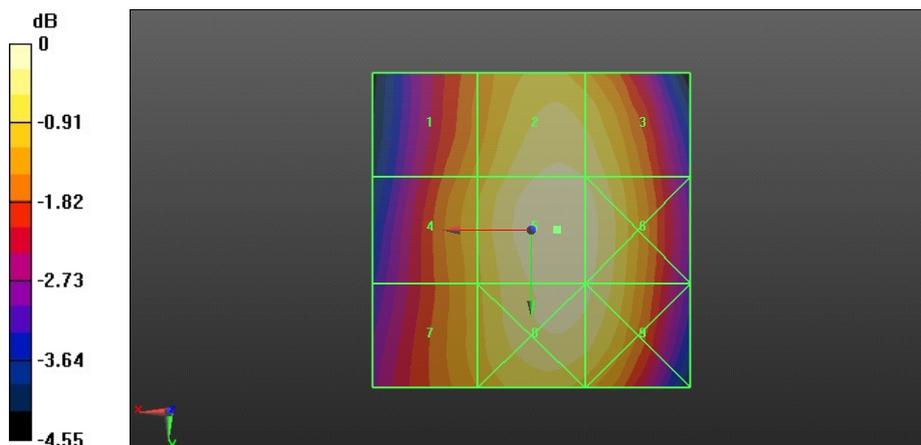
Grid 1 M3 180.1 V/m	Grid 2 M3 199.4 V/m	Grid 3 M3 197.1 V/m
Grid 4 M3 184.8 V/m	Grid 5 M3 204.4 V/m	Grid 6 M3 201.4 V/m
Grid 7 M3 182.5 V/m	Grid 8 M3 201.8 V/m	Grid 9 M3 199.4 V/m

Cursor:

Total = 204.4 V/m

E Category: M3

Location: -4, 0, 8.7 mm



0 dB = 204.4 V/m = 46.21 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM1900-810CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 20.94 V/m; Power Drift = 0.12 dB

PMF = 2.860 is applied.

E-field emissions = 70.75 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

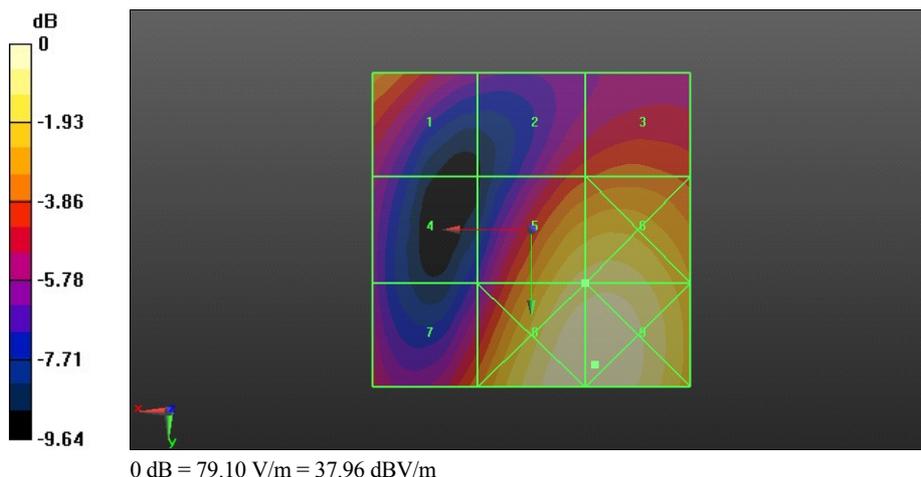
Grid 1 M3 57.05 V/m	Grid 2 M3 49.88 V/m	Grid 3 M3 52.89 V/m
Grid 4 M4 42.08 V/m	Grid 5 M3 70.75 V/m	Grid 6 M3 72.07 V/m
Grid 7 M3 53.52 V/m	Grid 8 M3 78.88 V/m	Grid 9 M3 79.10 V/m

Cursor:

Total = 79.10 V/m

E Category: M3

Location: -10, 21.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM1900-661CH**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.33 V/m; Power Drift = -0.17 dB

PMF = 2.860 is applied.

E-field emissions = 79.45 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

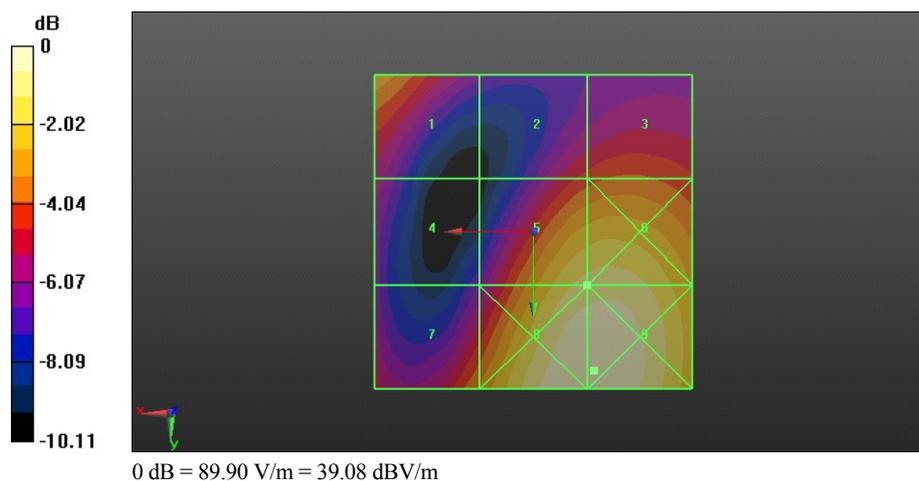
Grid 1 M3 65.04 V/m	Grid 2 M3 54.25 V/m	Grid 3 M3 57.39 V/m
Grid 4 M4 47.12 V/m	Grid 5 M3 79.45 V/m	Grid 6 M3 80.79 V/m
Grid 7 M3 61.95 V/m	Grid 8 M2 89.84 V/m	Grid 9 M2 89.90 V/m

Cursor:

Total = 89.90 V/m

E Category: M2

Location: -9.5, 22, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM1900-512CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.34 V/m; Power Drift = 0.08 dB

PMF = 2.860 is applied.

E-field emissions = 74.30 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

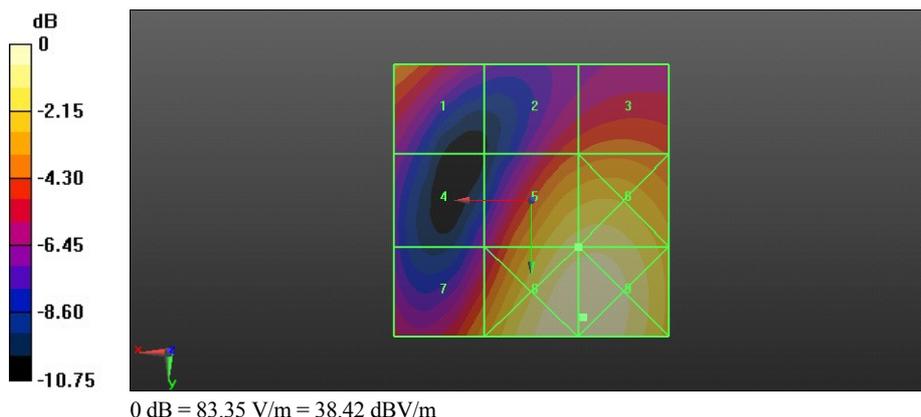
Grid 1 M3 56.99 V/m	Grid 2 M3 51.20 V/m	Grid 3 M3 54.22 V/m
Grid 4 M4 39.86 V/m	Grid 5 M3 74.30 V/m	Grid 6 M3 75.57 V/m
Grid 7 M3 58.46 V/m	Grid 8 M3 83.23 V/m	Grid 9 M3 83.35 V/m

Cursor:

Total = 83.35 V/m

E Category: M3

Location: -9.5, 21.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-GSM1900-661CH with battery 2#**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.25 V/m; Power Drift = 0.13 dB

PMF = 2.860 is applied.

E-field emissions = 80.72 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

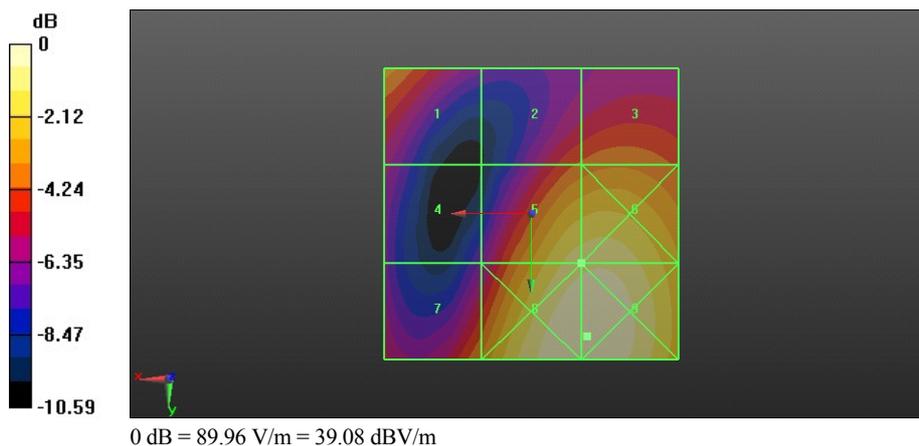
Grid 1 M3 63.05 V/m	Grid 2 M3 56.26 V/m	Grid 3 M3 59.24 V/m
Grid 4 M4 45.28 V/m	Grid 5 M3 80.72 V/m	Grid 6 M3 82.08 V/m
Grid 7 M3 61.15 V/m	Grid 8 M2 89.84 V/m	Grid 9 M2 89.96 V/m

Cursor:

Total = 89.96 V/m

E Category: M2

Location: -9.5, 21, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band II-9538CH**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.53 V/m; Power Drift = 0.00 dB

PMF = 1.020 is applied.

E-field emissions = 36.07 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

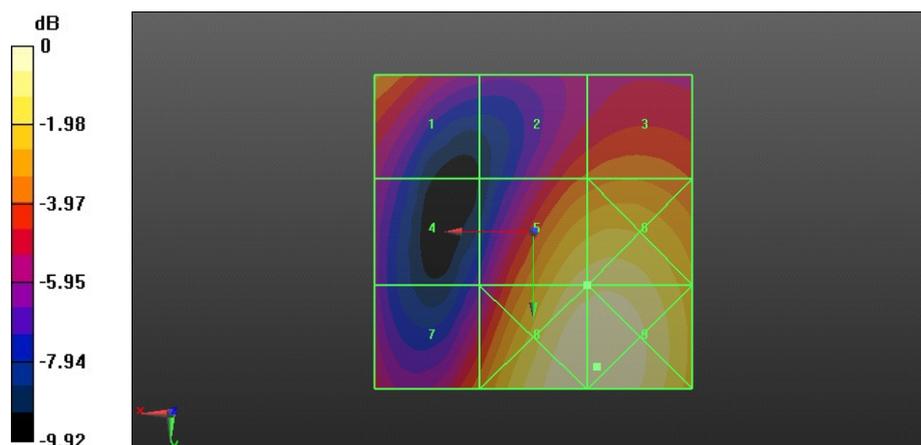
Grid 1 M4 28.13 V/m	Grid 2 M4 25.96 V/m	Grid 3 M4 27.33 V/m
Grid 4 M4 20.80 V/m	Grid 5 M4 36.07 V/m	Grid 6 M4 36.72 V/m
Grid 7 M4 26.83 V/m	Grid 8 M4 40.01 V/m	Grid 9 M4 40.10 V/m

Cursor:

Total = 40.10 V/m

E Category: M4

Location: -10, 21.5, 8.7 mm



0 dB = 40.10 V/m = 32.06 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band II-9400CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 29.95 V/m; Power Drift = 0.17 dB

PMF = 1.020 is applied.

E-field emissions = 36.00 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

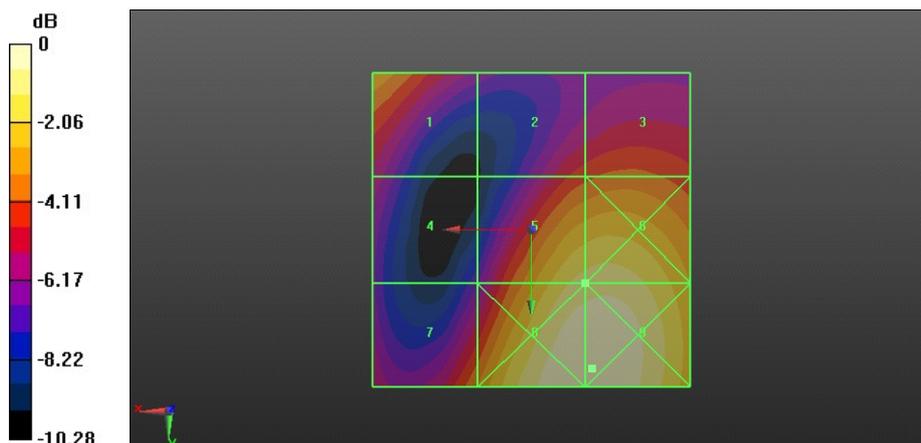
Grid 1 M4 29.64 V/m	Grid 2 M4 24.75 V/m	Grid 3 M4 26.08 V/m
Grid 4 M4 21.38 V/m	Grid 5 M4 36.00 V/m	Grid 6 M4 36.61 V/m
Grid 7 M4 27.64 V/m	Grid 8 M4 40.66 V/m	Grid 9 M4 40.70 V/m

Cursor:

Total = 40.70 V/m

E Category: M4

Location: -9.5, 22, 8.7 mm



0 dB = 40.70 V/m = 32.19 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band II-9262CH**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 31.23 V/m; Power Drift = 0.12 dB

PMF = 1.020 is applied.

E-field emissions = 37.11 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

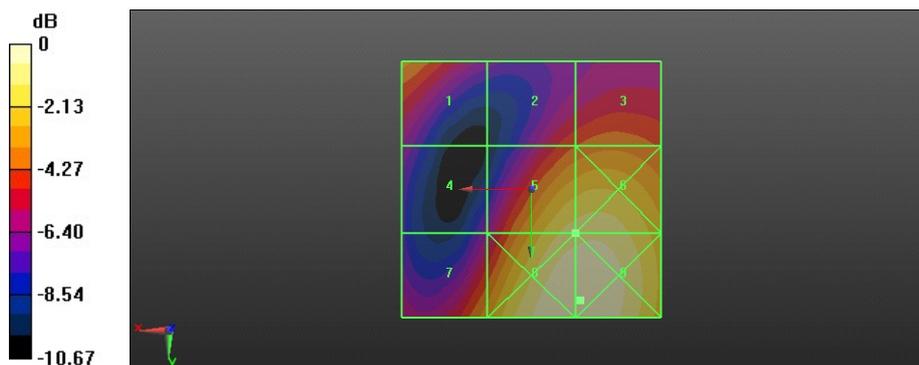
Grid 1 M4 28.90 V/m	Grid 2 M4 25.52 V/m	Grid 3 M4 27.22 V/m
Grid 4 M4 20.11 V/m	Grid 5 M4 37.11 V/m	Grid 6 M4 37.78 V/m
Grid 7 M4 29.59 V/m	Grid 8 M4 41.71 V/m	Grid 9 M4 41.74 V/m

Cursor:

Total = 41.74 V/m

E Category: M4

Location: -9.5, 21.5, 8.7 mm



0 dB = 41.74 V/m = 32.41 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band II-9262CH with battery 2#**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 32.60 V/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

E-field emissions = 38.32 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

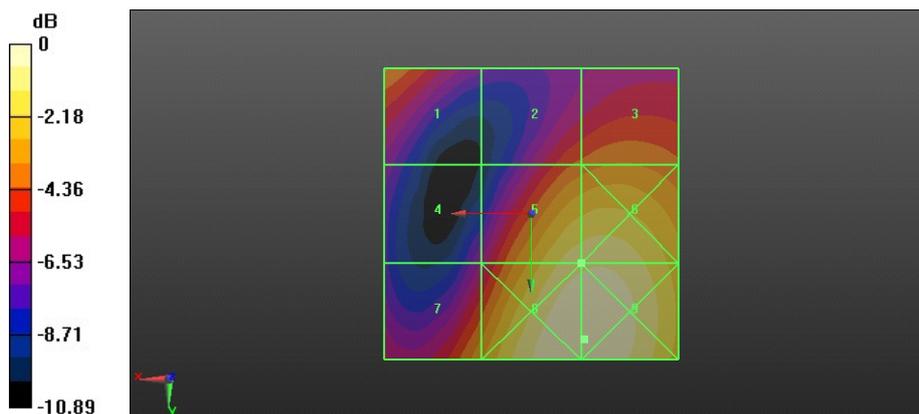
Grid 1 M4 28.53 V/m	Grid 2 M4 26.51 V/m	Grid 3 M4 28.24 V/m
Grid 4 M4 20.43 V/m	Grid 5 M4 38.32 V/m	Grid 6 M4 38.87 V/m
Grid 7 M4 30.23 V/m	Grid 8 M4 42.54 V/m	Grid 9 M4 42.55 V/m

Cursor:

Total = 42.55 V/m

E Category: M4

Location: -9, 21.5, 8.7 mm



0 dB = 42.55 V/m = 32.58 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band IV-1513CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 31.97 V/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

E-field emissions = 36.79 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

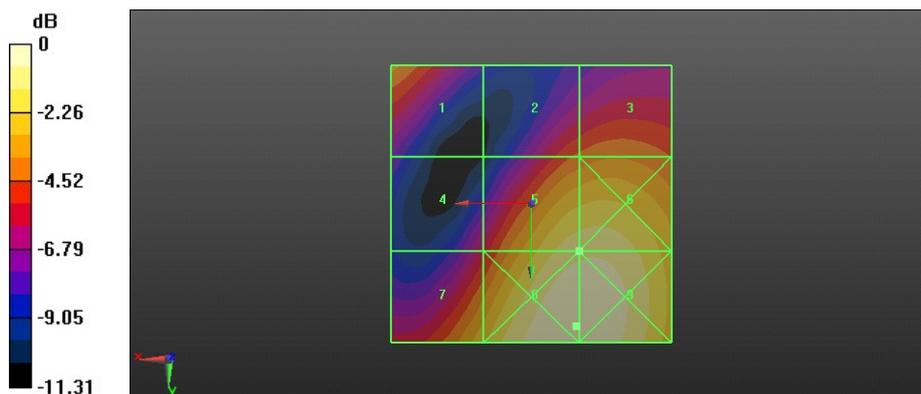
Grid 1 M4 27.68 V/m	Grid 2 M4 25.08 V/m	Grid 3 M4 26.53 V/m
Grid 4 M4 21.40 V/m	Grid 5 M4 36.79 V/m	Grid 6 M4 37.16 V/m
Grid 7 M4 31.35 V/m	Grid 8 M4 41.17 V/m	Grid 9 M4 41.17 V/m

Cursor:

Total = 41.17 V/m

E Category: M4

Location: -8, 22, 8.7 mm



0 dB = 41.17 V/m = 32.29 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band IV-1413CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 32.35 V/m; Power Drift = 0.03 dB

PMF = 1.020 is applied.

E-field emissions = 37.13 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

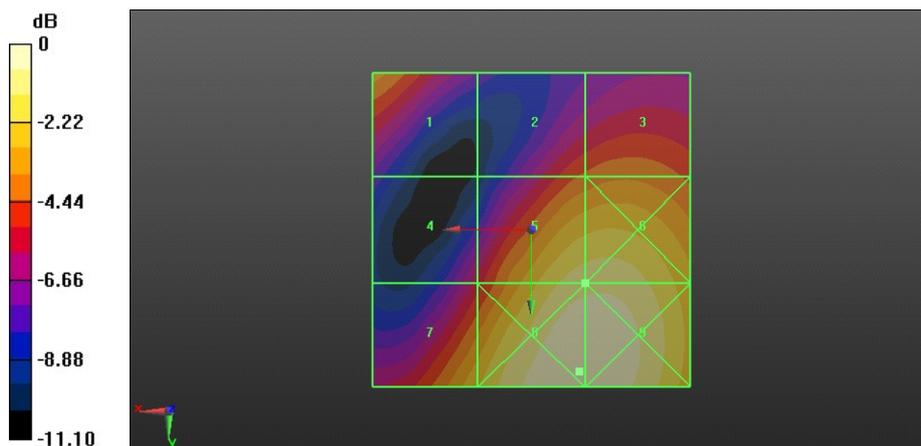
Grid 1 M4 28.60 V/m	Grid 2 M4 25.55 V/m	Grid 3 M4 26.89 V/m
Grid 4 M4 21.98 V/m	Grid 5 M4 37.13 V/m	Grid 6 M4 37.46 V/m
Grid 7 M4 32.08 V/m	Grid 8 M4 41.65 V/m	Grid 9 M4 41.63 V/m

Cursor:

Total = 41.65 V/m

E Category: M4

Location: -7.5, 22.5, 8.7 mm



0 dB = 41.65 V/m = 32.39 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band IV-1312CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 40.28 V/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

E-field emissions = 45.03 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

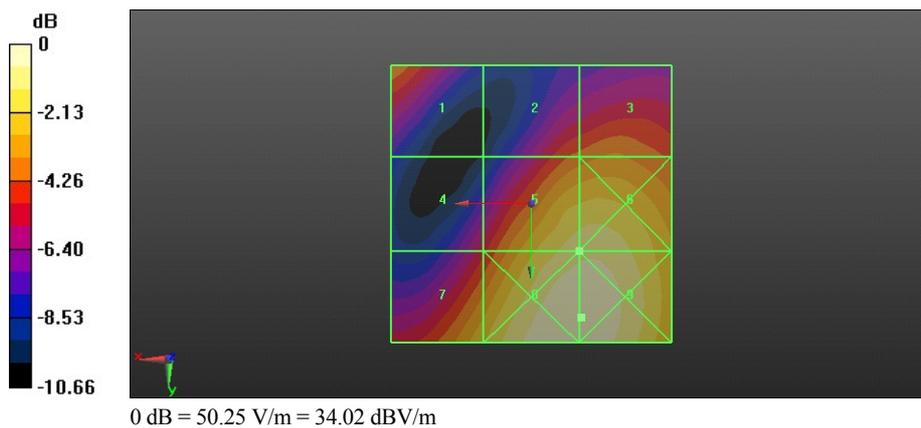
Grid 1 M4 33.41 V/m	Grid 2 M4 31.77 V/m	Grid 3 M4 33.88 V/m
Grid 4 M4 27.83 V/m	Grid 5 M4 45.03 V/m	Grid 6 M4 45.55 V/m
Grid 7 M4 39.16 V/m	Grid 8 M4 50.23 V/m	Grid 9 M4 50.25 V/m

Cursor:

Total = 50.25 V/m

E Category: M4

Location: -9, 20.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band IV-1312CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 39.39 V/m; Power Drift = 0.08 dB

PMF = 1.020 is applied.

E-field emissions = 44.18 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

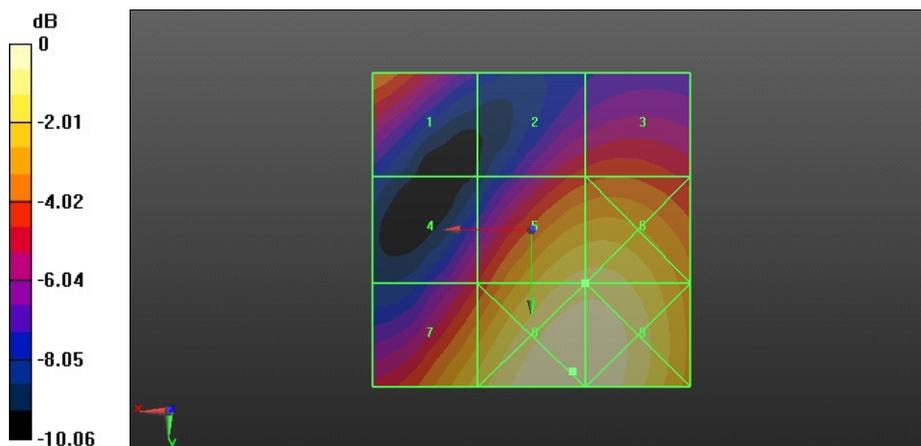
Grid 1 M4 34.09 V/m	Grid 2 M4 30.17 V/m	Grid 3 M4 31.15 V/m
Grid 4 M4 28.87 V/m	Grid 5 M4 44.18 V/m	Grid 6 M4 44.31 V/m
Grid 7 M4 40.90 V/m	Grid 8 M4 49.61 V/m	Grid 9 M4 49.38 V/m

Cursor:

Total = 49.61 V/m

E Category: M4

Location: -6.5, 22.5, 8.7 mm



0 dB = 49.61 V/m = 33.91 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band V-4233CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 71.78 V/m; Power Drift = -0.04 dB

PMF = 1.040 is applied.

E-field emissions = 59.27 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

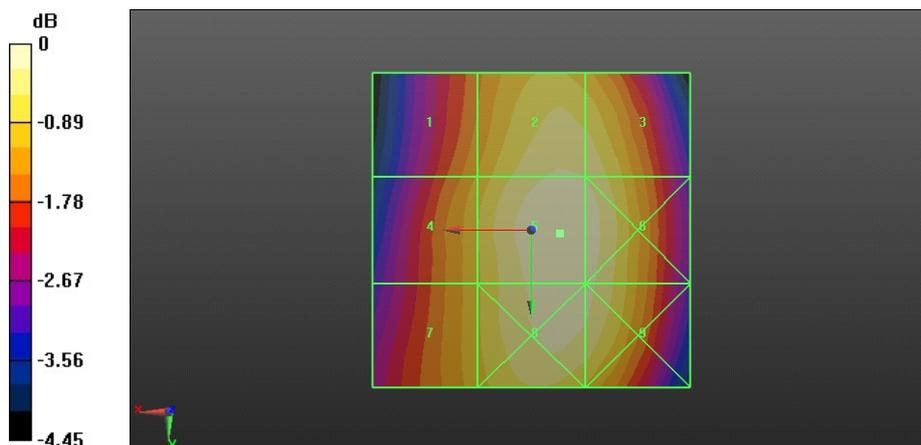
Grid 1 M4 51.93 V/m	Grid 2 M4 57.57 V/m	Grid 3 M4 57.18 V/m
Grid 4 M4 53.43 V/m	Grid 5 M4 59.27 V/m	Grid 6 M4 58.57 V/m
Grid 7 M4 53.22 V/m	Grid 8 M4 58.77 V/m	Grid 9 M4 58.03 V/m

Cursor:

Total = 59.27 V/m

E Category: M4

Location: -4.5, 0.5, 8.7 mm



0 dB = 59.27 V/m = 35.46 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band V-4182CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 74.15 V/m; Power Drift = 0.04 dB

PMF = 1.040 is applied.

E-field emissions = 61.62 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

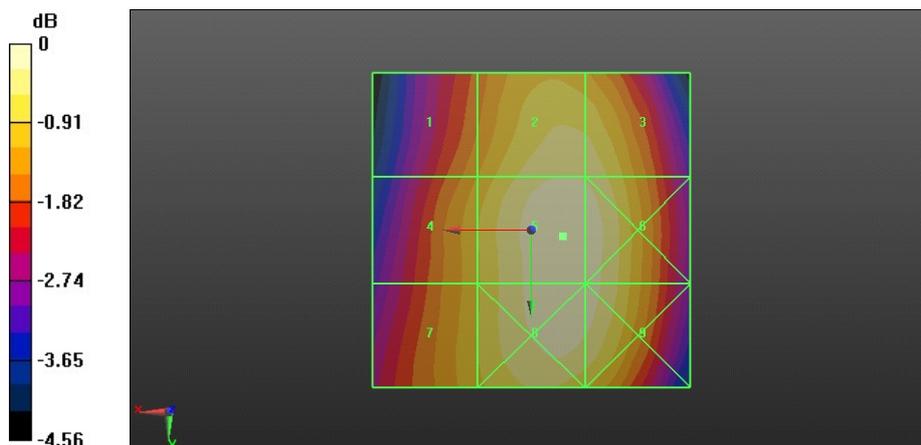
Grid 1 M4 53.55 V/m	Grid 2 M4 59.56 V/m	Grid 3 M4 59.29 V/m
Grid 4 M4 55.45 V/m	Grid 5 M4 61.62 V/m	Grid 6 M4 61.04 V/m
Grid 7 M4 55.46 V/m	Grid 8 M4 61.43 V/m	Grid 9 M4 60.80 V/m

Cursor:

Total = 61.62 V/m

E Category: M4

Location: -5, 1, 8.7 mm



0 dB = 61.62 V/m = 35.79 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band V-4132CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 70.89 V/m; Power Drift = -0.02 dB

PMF = 1.040 is applied.

E-field emissions = 58.52 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

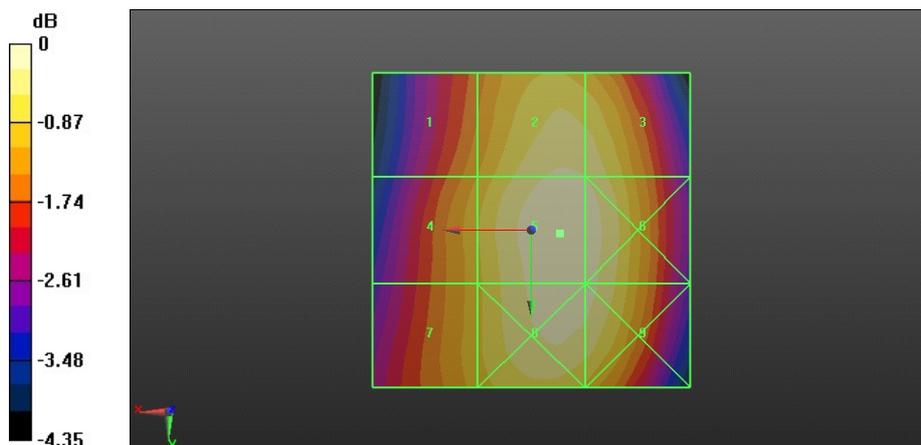
Grid 1 M4 51.24 V/m	Grid 2 M4 56.97 V/m	Grid 3 M4 56.56 V/m
Grid 4 M4 52.83 V/m	Grid 5 M4 58.52 V/m	Grid 6 M4 57.91 V/m
Grid 7 M4 52.55 V/m	Grid 8 M4 58.06 V/m	Grid 9 M4 57.47 V/m

Cursor:

Total = 58.52 V/m

E Category: M4

Location: -4.5, 0.5, 8.7 mm



0 dB = 58.52 V/m = 35.35 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A1-UMTS Band V-4182CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 74.10 V/m; Power Drift = -0.04 dB

PMF = 1.040 is applied.

E-field emissions = 61.77 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

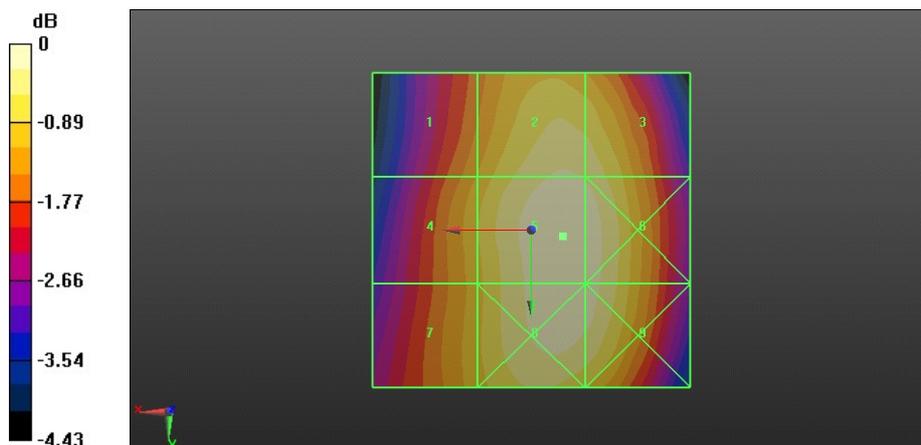
Grid 1 M4 54.08 V/m	Grid 2 M4 60.02 V/m	Grid 3 M4 59.51 V/m
Grid 4 M4 55.70 V/m	Grid 5 M4 61.77 V/m	Grid 6 M4 61.14 V/m
Grid 7 M4 55.39 V/m	Grid 8 M4 61.41 V/m	Grid 9 M4 60.88 V/m

Cursor:

Total = 61.77 V/m

E Category: M4

Location: -5, 1, 8.7 mm



0 dB = 61.77 V/m = 35.82 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM850-251CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09700 A/m; Power Drift = -0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.3328 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

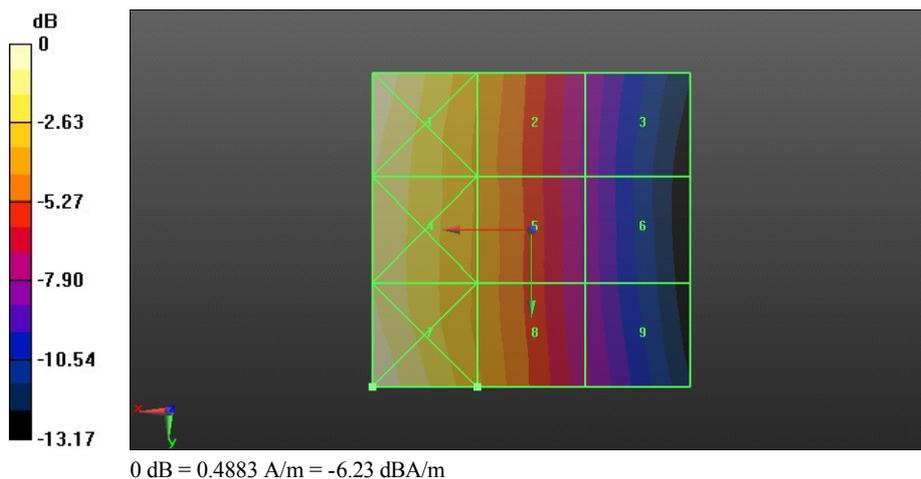
Grid 1 M3 0.479 A/m	Grid 2 M4 0.330 A/m	Grid 3 M4 0.196 A/m
Grid 4 M4 0.445 A/m	Grid 5 M4 0.322 A/m	Grid 6 M4 0.193 A/m
Grid 7 M3 0.488 A/m	Grid 8 M4 0.333 A/m	Grid 9 M4 0.203 A/m

Cursor:

Total = 0.4883 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM850-190CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08300 A/m; Power Drift = -0.08 dB

PMF = 2.820 is applied.

H-field emissions = 0.2960 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

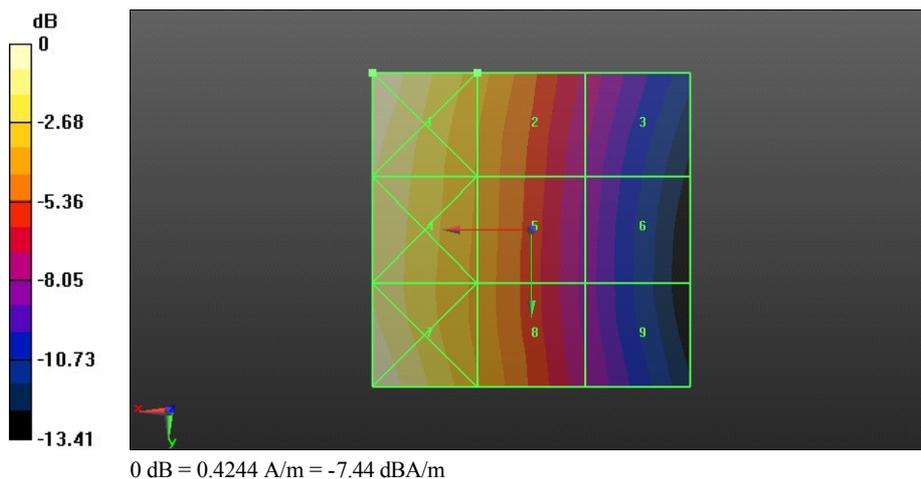
Grid 1 M4 0.424 A/m	Grid 2 M4 0.296 A/m	Grid 3 M4 0.182 A/m
Grid 4 M4 0.387 A/m	Grid 5 M4 0.279 A/m	Grid 6 M4 0.166 A/m
Grid 7 M4 0.422 A/m	Grid 8 M4 0.286 A/m	Grid 9 M4 0.172 A/m

Cursor:

Total = 0.4244 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM850-128CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07600 A/m; Power Drift = 0.06 dB

PMF = 2.832 is applied.

H-field emissions = 0.2688 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

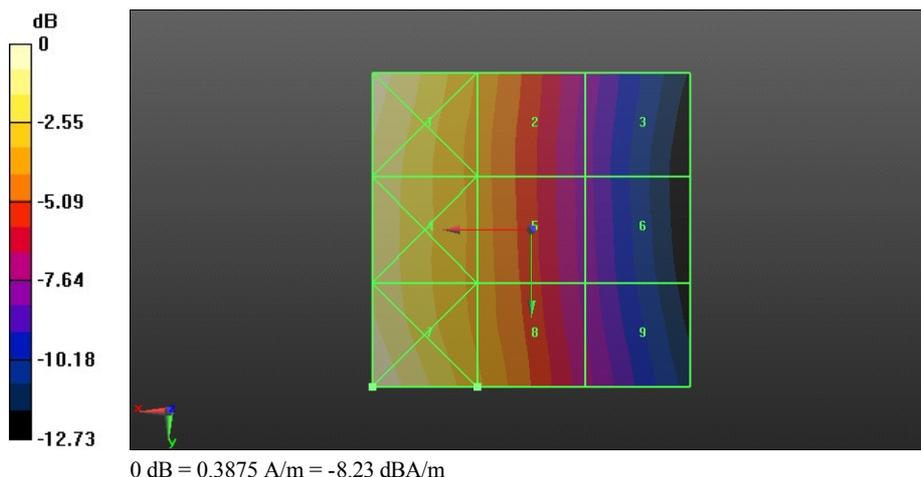
Grid 1 M4 0.373 A/m	Grid 2 M4 0.260 A/m	Grid 3 M4 0.158 A/m
Grid 4 M4 0.346 A/m	Grid 5 M4 0.253 A/m	Grid 6 M4 0.156 A/m
Grid 7 M4 0.388 A/m	Grid 8 M4 0.269 A/m	Grid 9 M4 0.168 A/m

Cursor:

Total = 0.3875 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM850-251CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09700 A/m; Power Drift = -0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.3359 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

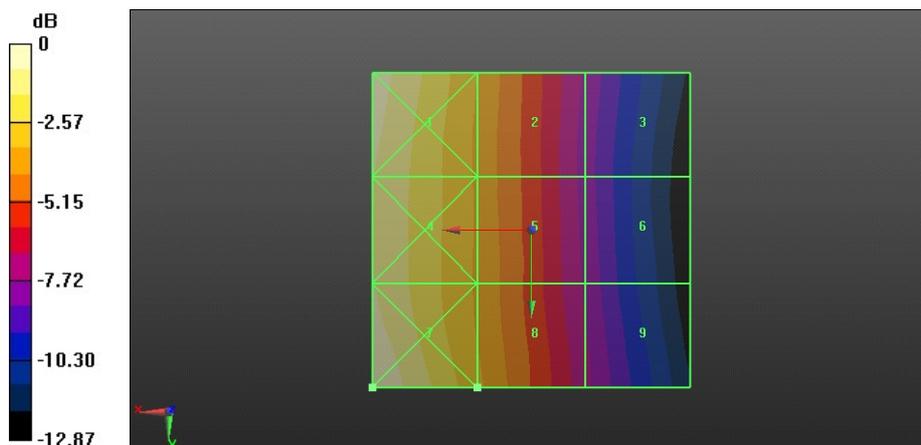
Grid 1 M3 0.468 A/m	Grid 2 M4 0.327 A/m	Grid 3 M4 0.197 A/m
Grid 4 M4 0.444 A/m	Grid 5 M4 0.323 A/m	Grid 6 M4 0.197 A/m
Grid 7 M3 0.485 A/m	Grid 8 M4 0.336 A/m	Grid 9 M4 0.206 A/m

Cursor:

Total = 0.4855 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.4855 A/m = -6.28 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM1900-810CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.06 dB

PMF = 2.830 is applied.

H-field emissions = 0.1976 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

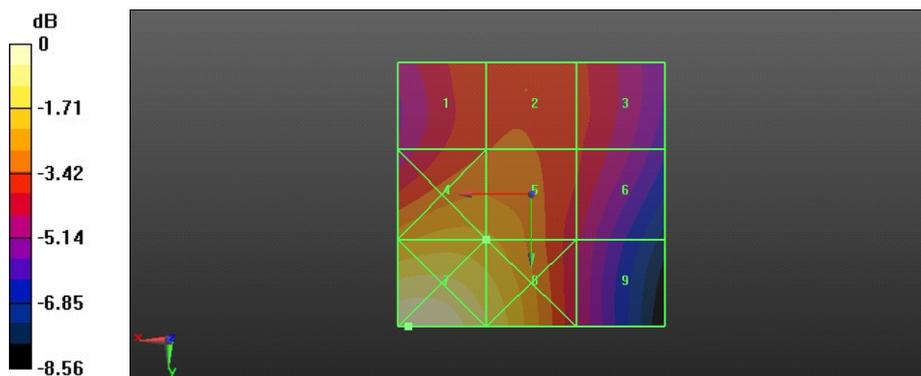
Grid 1 M3 0.171 A/m	Grid 2 M3 0.172 A/m	Grid 3 M3 0.164 A/m
Grid 4 M3 0.201 A/m	Grid 5 M3 0.198 A/m	Grid 6 M3 0.162 A/m
Grid 7 M2 0.253 A/m	Grid 8 M3 0.224 A/m	Grid 9 M3 0.153 A/m

Cursor:

Total = 0.2534 A/m

H Category: M2

Location: 23, 25, 8.7 mm



0 dB = 0.2534 A/m = -11.93 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM1900-661CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07800 A/m; Power Drift = 0.05 dB

PMF = 2.830 is applied.

H-field emissions = 0.2186 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

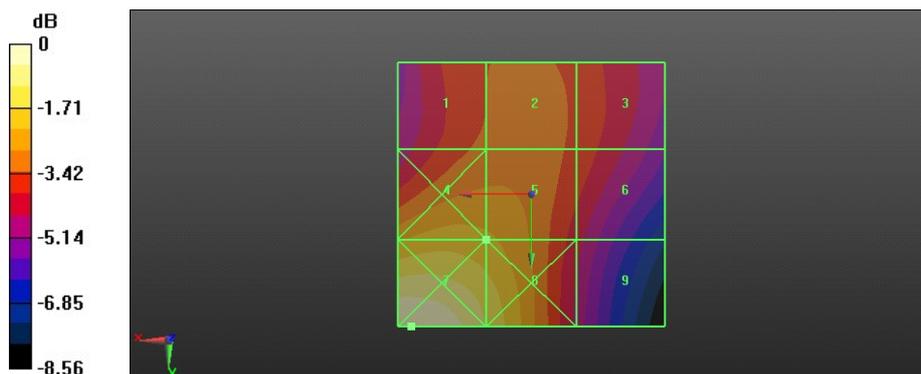
Grid 1 M3 0.193 A/m	Grid 2 M3 0.195 A/m	Grid 3 M3 0.187 A/m
Grid 4 M3 0.223 A/m	Grid 5 M3 0.219 A/m	Grid 6 M3 0.186 A/m
Grid 7 M2 0.280 A/m	Grid 8 M3 0.246 A/m	Grid 9 M3 0.171 A/m

Cursor:

Total = 0.2804 A/m

H Category: M2

Location: 22.5, 25, 8.7 mm



0 dB = 0.2804 A/m = -11.04 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM1900-512CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.03 dB

PMF = 2.830 is applied.

H-field emissions = 0.2038 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

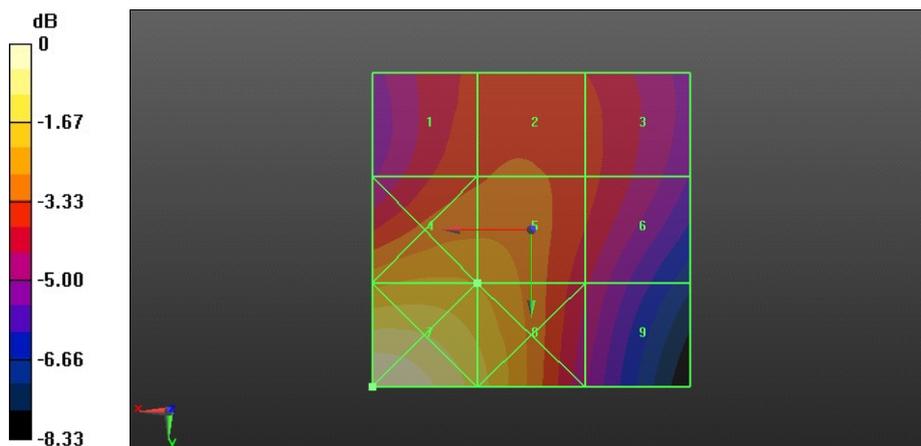
Grid 1 M3 0.178 A/m	Grid 2 M3 0.182 A/m	Grid 3 M3 0.173 A/m
Grid 4 M3 0.208 A/m	Grid 5 M3 0.204 A/m	Grid 6 M3 0.173 A/m
Grid 7 M2 0.264 A/m	Grid 8 M3 0.225 A/m	Grid 9 M3 0.161 A/m

Cursor:

Total = 0.2639 A/m

H Category: M2

Location: 25, 25, 8.7 mm



0 dB = 0.2639 A/m = -11.57 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-GSM1900-661CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07900 A/m; Power Drift = 0.06 dB

PMF = 2.830 is applied.

H-field emissions = 0.2164 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

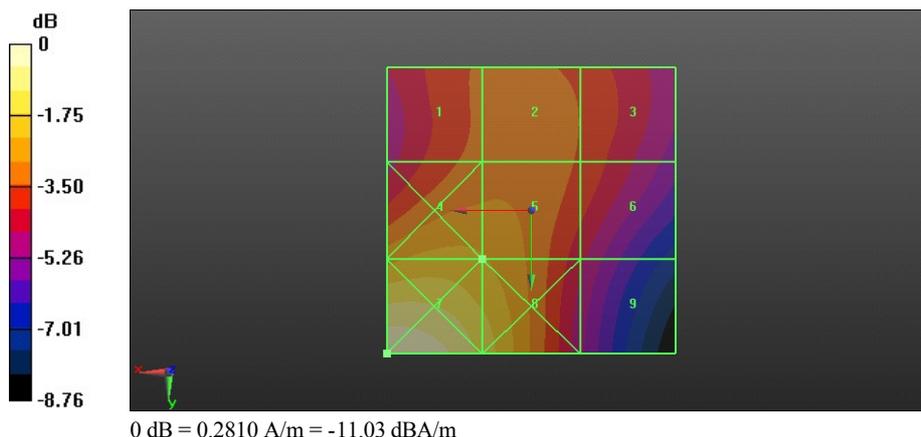
Grid 1 M3 0.193 A/m	Grid 2 M3 0.196 A/m	Grid 3 M3 0.188 A/m
Grid 4 M3 0.220 A/m	Grid 5 M3 0.216 A/m	Grid 6 M3 0.186 A/m
Grid 7 M2 0.281 A/m	Grid 8 M3 0.241 A/m	Grid 9 M3 0.167 A/m

Cursor:

Total = 0.2810 A/m

H Category: M2

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band II-9538CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09200 A/m; Power Drift = -0.00 dB

PMF = 1.010 is applied.

H-field emissions = 0.09337 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

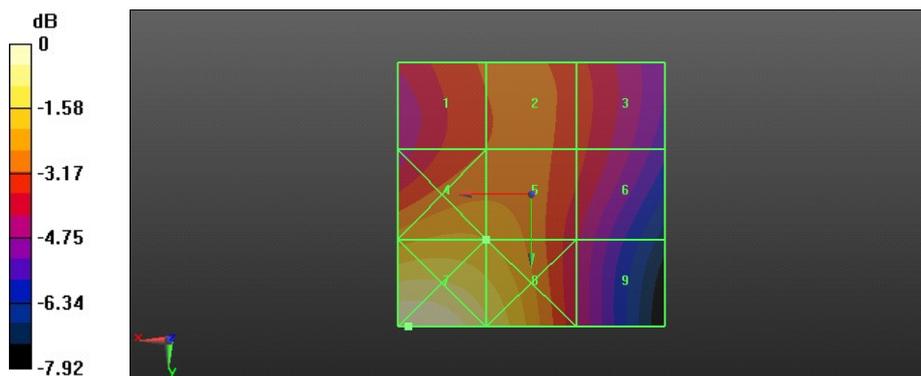
Grid 1 M4 0.083 A/m	Grid 2 M4 0.084 A/m	Grid 3 M4 0.080 A/m
Grid 4 M4 0.095 A/m	Grid 5 M4 0.093 A/m	Grid 6 M4 0.080 A/m
Grid 7 M4 0.119 A/m	Grid 8 M4 0.107 A/m	Grid 9 M4 0.074 A/m

Cursor:

Total = 0.1190 A/m

H Category: M4

Location: 23, 25, 8.7 mm



0 dB = 0.1190 A/m = -18.49 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band II-9400CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09500 A/m; Power Drift = 0.03 dB

PMF = 1.010 is applied.

H-field emissions = 0.09287 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

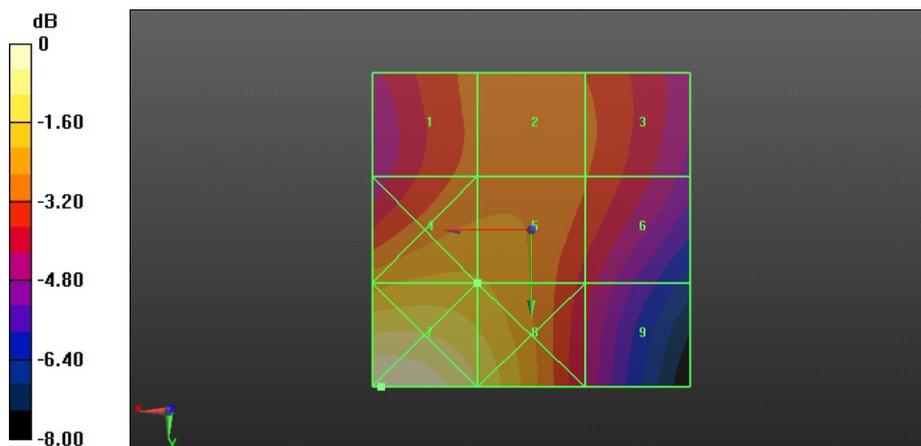
Grid 1 M4 0.084 A/m	Grid 2 M4 0.086 A/m	Grid 3 M4 0.083 A/m
Grid 4 M4 0.094 A/m	Grid 5 M4 0.093 A/m	Grid 6 M4 0.082 A/m
Grid 7 M4 0.118 A/m	Grid 8 M4 0.105 A/m	Grid 9 M4 0.075 A/m

Cursor:

Total = 0.1176 A/m

H Category: M4

Location: 23.5, 25, 8.7 mm



0 dB = 0.1176 A/m = -18.59 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band II-9262CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09900 A/m; Power Drift = 0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.09672 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

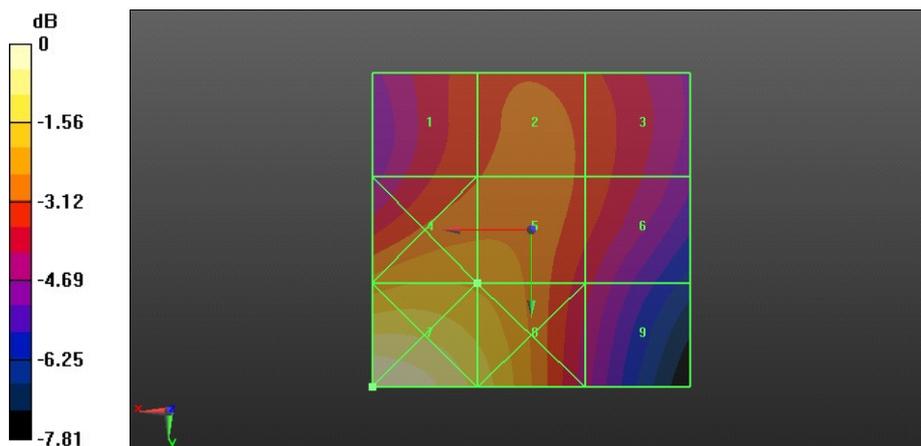
Grid 1 M4 0.086 A/m	Grid 2 M4 0.089 A/m	Grid 3 M4 0.086 A/m
Grid 4 M4 0.098 A/m	Grid 5 M4 0.097 A/m	Grid 6 M4 0.085 A/m
Grid 7 M4 0.124 A/m	Grid 8 M4 0.108 A/m	Grid 9 M4 0.079 A/m

Cursor:

Total = 0.1240 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1240 A/m = -18.13 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band II-9262CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1040 A/m; Power Drift = -0.04 dB

PMF = 1.010 is applied.

H-field emissions = 0.09891 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

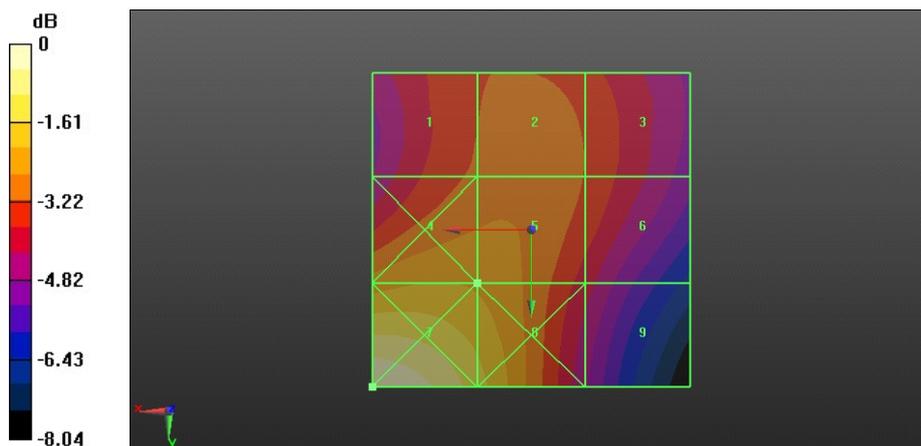
Grid 1 M4 0.090 A/m	Grid 2 M4 0.092 A/m	Grid 3 M4 0.088 A/m
Grid 4 M4 0.100 A/m	Grid 5 M4 0.099 A/m	Grid 6 M4 0.088 A/m
Grid 7 M4 0.128 A/m	Grid 8 M4 0.109 A/m	Grid 9 M4 0.080 A/m

Cursor:

Total = 0.1277 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1277 A/m = -17.87 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band IV-1513CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1050 A/m; Power Drift = -0.01 dB

PMF = 0.9800 is applied.

H-field emissions = 0.09749 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

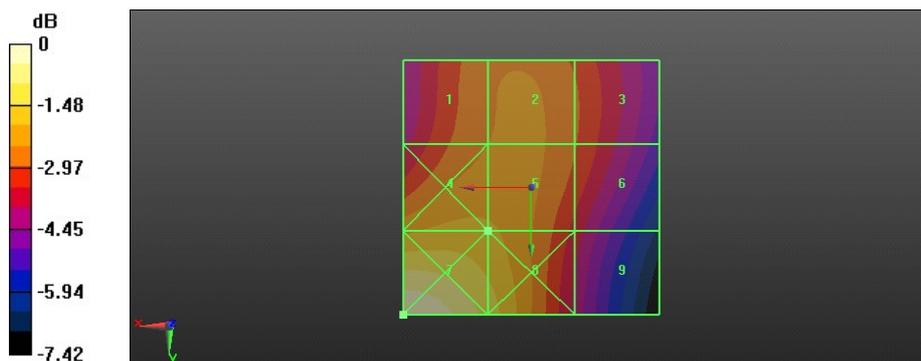
Grid 1 M4 0.091 A/m	Grid 2 M4 0.093 A/m	Grid 3 M4 0.087 A/m
Grid 4 M4 0.098 A/m	Grid 5 M4 0.097 A/m	Grid 6 M4 0.087 A/m
Grid 7 M4 0.121 A/m	Grid 8 M4 0.106 A/m	Grid 9 M4 0.080 A/m

Cursor:

Total = 0.1212 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1212 A/m = -18.33 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band IV-1413CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1040 A/m; Power Drift = -0.04 dB

PMF = 0.9800 is applied.

H-field emissions = 0.09816 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

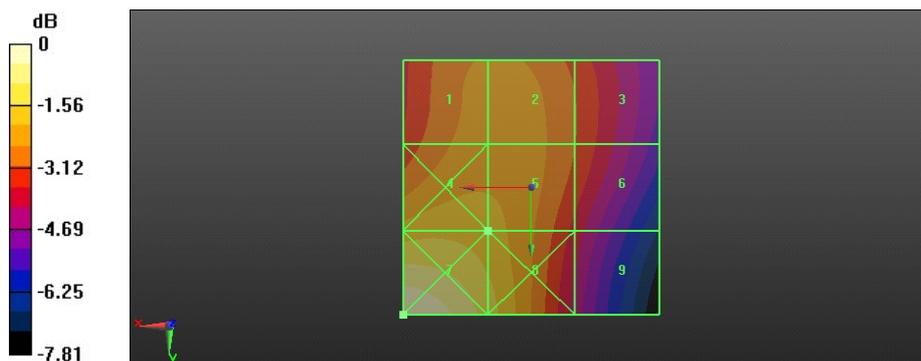
Grid 1 M4 0.093 A/m	Grid 2 M4 0.093 A/m	Grid 3 M4 0.085 A/m
Grid 4 M4 0.100 A/m	Grid 5 M4 0.098 A/m	Grid 6 M4 0.085 A/m
Grid 7 M4 0.122 A/m	Grid 8 M4 0.105 A/m	Grid 9 M4 0.078 A/m

Cursor:

Total = 0.1216 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1216 A/m = -18.30 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band IV-1312CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1180 A/m; Power Drift = 0.02 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1107 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

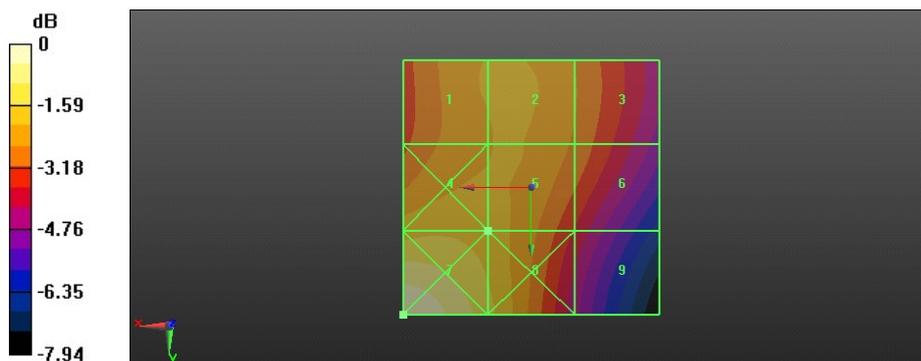
Grid 1 M4 0.108 A/m	Grid 2 M4 0.109 A/m	Grid 3 M4 0.102 A/m
Grid 4 M4 0.113 A/m	Grid 5 M4 0.111 A/m	Grid 6 M4 0.100 A/m
Grid 7 M4 0.137 A/m	Grid 8 M4 0.117 A/m	Grid 9 M4 0.089 A/m

Cursor:

Total = 0.1372 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1372 A/m = -17.25 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band IV-1312CH with battery 2#**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1170 A/m; Power Drift = 0.03 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1052 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

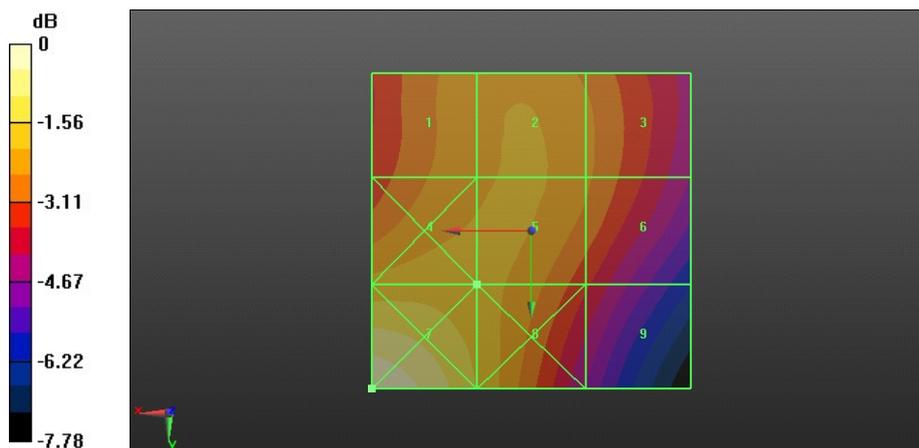
Grid 1 M4 0.102 A/m	Grid 2 M4 0.104 A/m	Grid 3 M4 0.099 A/m
Grid 4 M4 0.107 A/m	Grid 5 M4 0.105 A/m	Grid 6 M4 0.098 A/m
Grid 7 M4 0.131 A/m	Grid 8 M4 0.109 A/m	Grid 9 M4 0.088 A/m

Cursor:

Total = 0.1309 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1309 A/m = -17.66 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band V-4233CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07200 A/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.09064 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

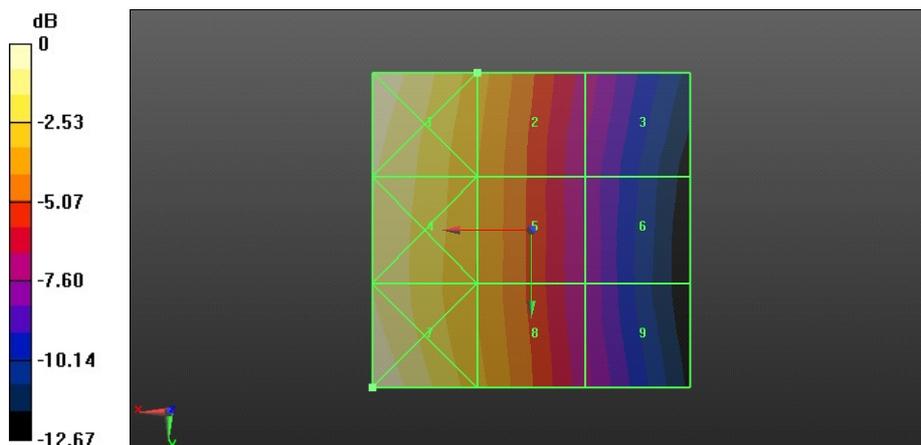
Grid 1 M4 0.125 A/m	Grid 2 M4 0.091 A/m	Grid 3 M4 0.056 A/m
Grid 4 M4 0.117 A/m	Grid 5 M4 0.087 A/m	Grid 6 M4 0.053 A/m
Grid 7 M4 0.128 A/m	Grid 8 M4 0.090 A/m	Grid 9 M4 0.055 A/m

Cursor:

Total = 0.1275 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1275 A/m = -17.89 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band V-4182CH**DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07200 A/m; Power Drift = -0.00 dB

PMF = 1.020 is applied.

H-field emissions = 0.09303 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

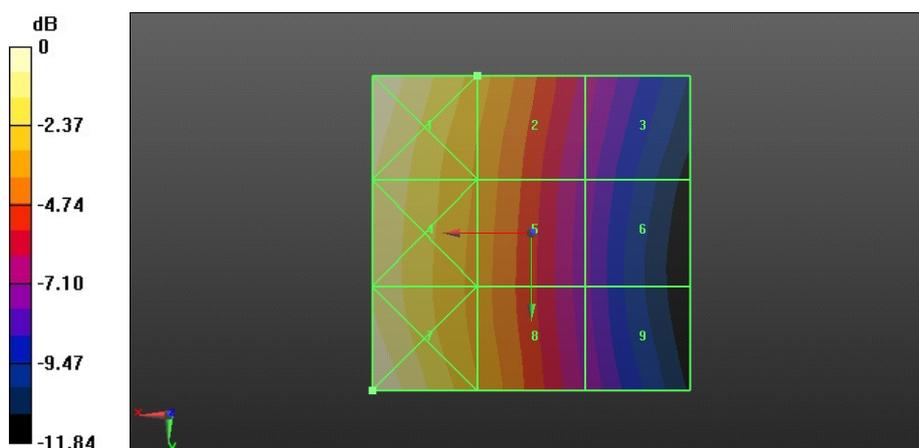
Grid 1 M4 0.127 A/m	Grid 2 M4 0.093 A/m	Grid 3 M4 0.059 A/m
Grid 4 M4 0.117 A/m	Grid 5 M4 0.087 A/m	Grid 6 M4 0.054 A/m
Grid 7 M4 0.127 A/m	Grid 8 M4 0.089 A/m	Grid 9 M4 0.056 A/m

Cursor:

Total = 0.1272 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1272 A/m = -17.91 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band V-4132CH

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07100 A/m; Power Drift = -0.05 dB

PMF = 1.020 is applied.

H-field emissions = 0.09065 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

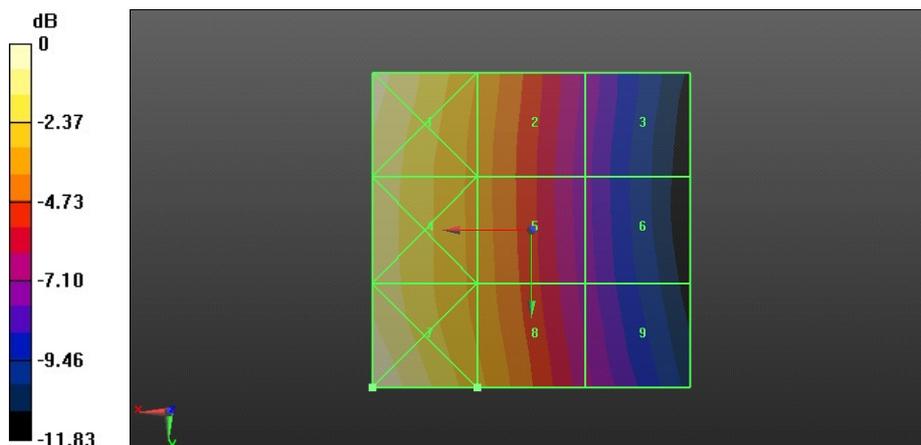
Grid 1 M4 0.121 A/m	Grid 2 M4 0.088 A/m	Grid 3 M4 0.055 A/m
Grid 4 M4 0.113 A/m	Grid 5 M4 0.085 A/m	Grid 6 M4 0.054 A/m
Grid 7 M4 0.126 A/m	Grid 8 M4 0.091 A/m	Grid 9 M4 0.058 A/m

Cursor:

Total = 0.1262 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1262 A/m = -17.98 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A1-UMTS Band V-4182CH with battery 2#

DUT: Y301-A1; Type: UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.00 dB

PMF = 1.020 is applied.

H-field emissions = 0.09346 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

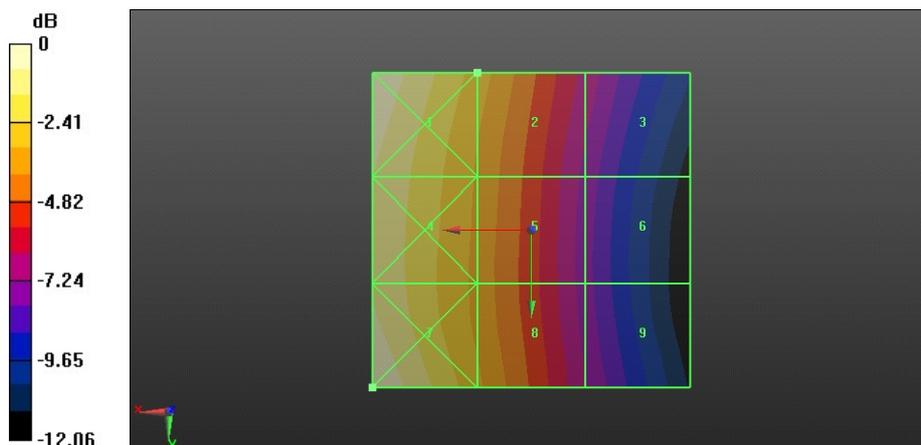
Grid 1 M4 0.128 A/m	Grid 2 M4 0.093 A/m	Grid 3 M4 0.060 A/m
Grid 4 M4 0.117 A/m	Grid 5 M4 0.088 A/m	Grid 6 M4 0.054 A/m
Grid 7 M4 0.128 A/m	Grid 8 M4 0.091 A/m	Grid 9 M4 0.056 A/m

Cursor:

Total = 0.1285 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1285 A/m = -17.82 dBA/m